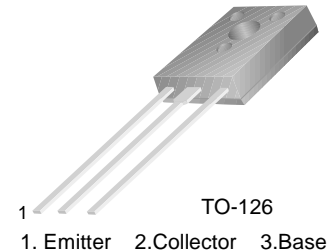


KSE200

Feature

- Low Collector-Emitter Saturation Voltage
- High Current Gain Bandwidth Product : $f_T=65\text{MHz}$ @ $I_C=100\text{mA}$ (Min.)
- Complement to KSE210



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter- Base Voltage	8	V
I_C	Collector Current	5	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	15	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}, I_B=0$	25		V
I_{CBO}	Collector Cut-off Current	$V_{CB}=40\text{V}, I_E=0$ $V_{CB}=40\text{V}, I_E=0$ @ $T_J=125^\circ\text{C}$		100 100	nA μA
I_{EBO}	Emitter Cut-off Current	$V_{BE}=8\text{V}, I_C=0$		100	nA
h_{FE}	DC Current Gain	$V_{CE}=1\text{V}, I_C=500\text{mA}$ $V_{CE}=1\text{V}, I_C=2\text{A}$ $V_{CE}=2\text{V}, I_C=5\text{A}$	70 45 10	180	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=500\text{mA}, I_B=50\text{mA}$ $I_C=2\text{A}, I_C=200\text{mA}$ $I_C=5\text{A}, I_B=1\text{A}$		0.3 0.75 1.8	V V V
$V_{BE(sat)}$	Base- Emitter Saturation Voltage	$I_C=5\text{A}, I_B=1\text{A}$		2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE}=1\text{V}, I_C=2\text{A}$		1.6	V
f_T	Current Gain Bandwidth Product	$V_{CE}=10\text{V}, I_C=100\text{mA}$	65		MHz
C_{ob}	Output Capacitance	$V_{CB}=10\text{V}, I_E=0, f=0.1\text{MHz}$		80	pF

Typical Characteristics

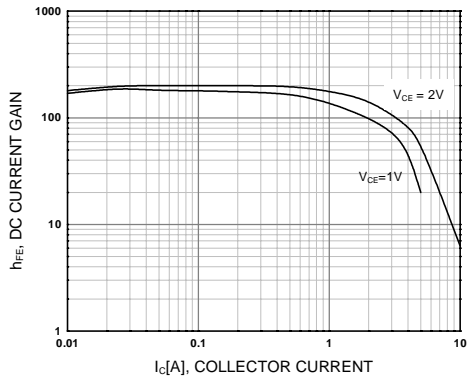


Figure 1. DC current Gain

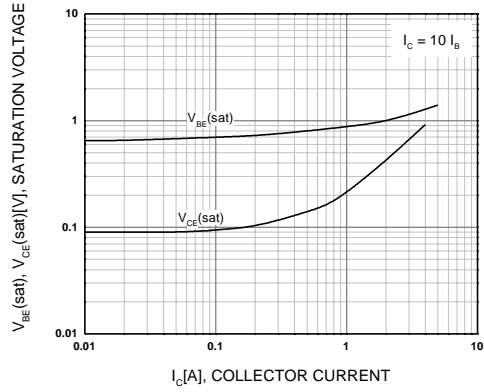


Figure 2. Collector-Emitter Saturation Voltage
Base-Emitter Saturation Voltage

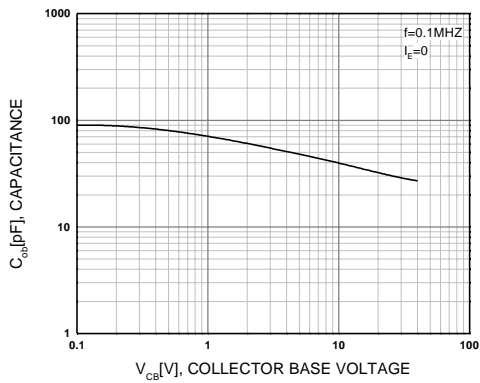


Figure 3. Collector Output Capacitance

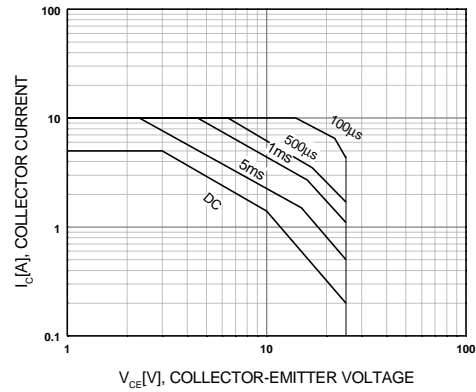


Figure 4. Forward Bias Safe Operating Area

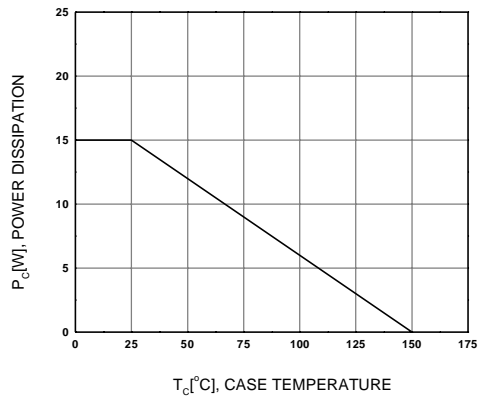


Figure 5. Power Derating

Package Dimensions

KSE200

TO-126



Dimensions in Millimeters

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E ² CMOS™	LittleFET™	Quiet Series™	VCX™
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